XN04407 (XN4407)

Silicon PNP epitaxial planar transistor

For general amplification

■ Features

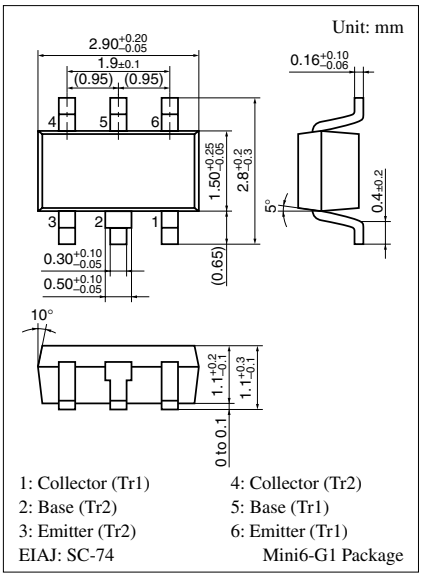
- Two elements incorporated into one package (Each transistor is separated)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number of Element

- 2SB0709A (2SB709A) + 2SB0970 (2SB970)

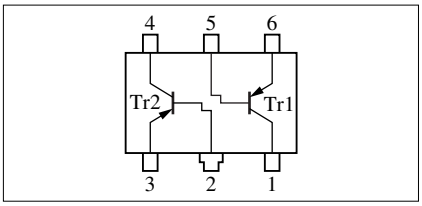
■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Tr1	Collector to base voltage	V_{CBO}	−60	V
	Collector to emitter voltage	V_{CEO}	−50	V
	Emitter to base voltage	V_{EBO}	−7	V
	Collector current	I_C	−100	mA
	Peak collector current	I_{CP}	−200	mA
Tr2	Collector to base voltage	V_{CBO}	−15	V
	Collector to emitter voltage	V_{CEO}	−10	V
	Emitter to base voltage	V_{EBO}	−7	V
	Collector current	I_C	−500	mA
	Peak collector current	I_{CP}	−1	A
Total	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	°C
	Storage temperature	T_{stg}	−55 to +150	°C



Marking Symbol: ES

Internal Connection



Note) The part number in the parenthesis shows conventional part number.

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10$ µA, $I_E = 0$	−60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2$ mA, $I_B = 0$	−50			V
Emitter to base voltage	V_{EBO}	$I_E = -10$ µA, $I_C = 0$	−7			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20$ V, $I_E = 0$			− 0.1	µA
	I_{CEO}	$V_{CE} = -10$ V, $I_B = 0$			−100	
DC current gain	h_{FE}	$V_{CE} = -10$ V, $I_C = -2$ mA	160		460	—
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100$ mA, $I_B = -10$ mA		− 0.3	− 0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		2.7		pF
Gain bandwidth product	f_T	$V_{CB} = -10$ V, $I_E = 1$ mA, f = 200 MHz		80		MHz

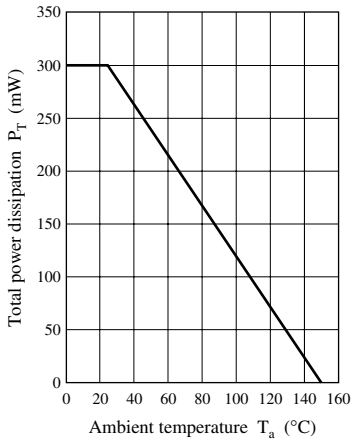
• Tr2

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10$ µA, $I_E = 0$	−15			V
Collector to emitter voltage	V_{CEO}	$I_C = -1$ mA, $I_B = 0$	−10			V
Emitter to base voltage	V_{EBO}	$I_E = -10$ µA, $I_C = 0$	−7			V
Collector cutoff current	I_{CBO}	$V_{CB} = -10$ V, $I_E = 0$			− 0.1	µA
DC current gain *	h_{FE1}	$V_{CE} = -2$ V, $I_C = -500$ mA	100		350	—
	h_{FE2}	$V_{CE} = -2$ V, $I_C = -1$ A	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -400$ mA, $I_B = -8$ mA		− 0.16	− 0.3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -400$ mA, $I_B = -8$ mA		− 0.8	−1.2	V
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		22		pF
Gain bandwidth product	f_T	$V_{CB} = -10$ V, $I_E = 50$ mA, f = 200 MHz		130		MHz

Note) ∗: Pulse test

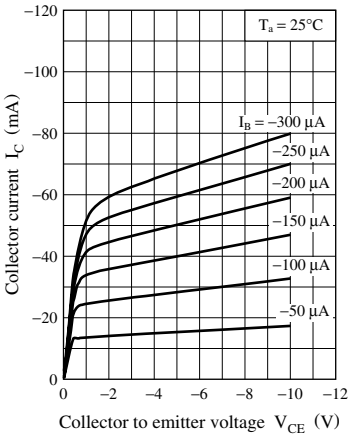
Common characteristics chart

P_T — T_a

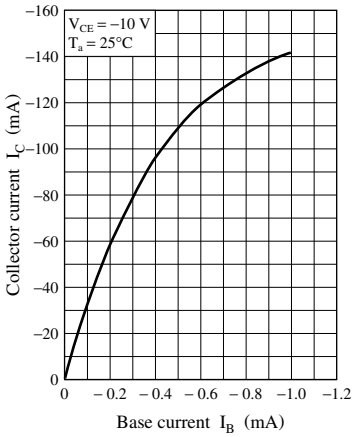


Characteristics chart of Tr1

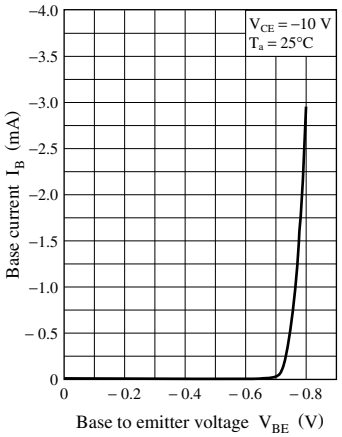
I_C — V_{CE}



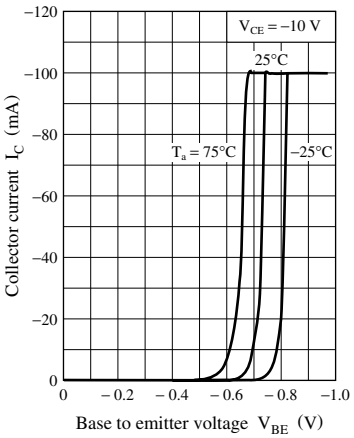
I_C — I_B



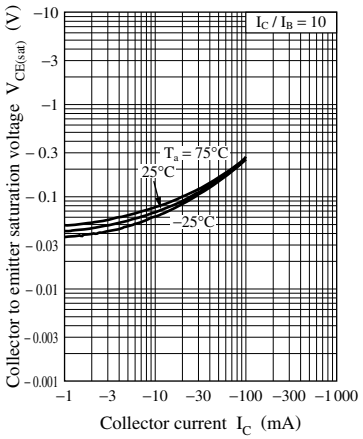
I_B — V_{BE}



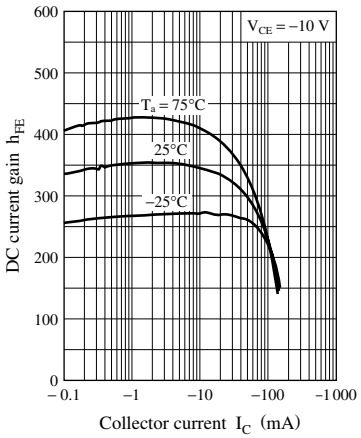
I_C — V_{BE}



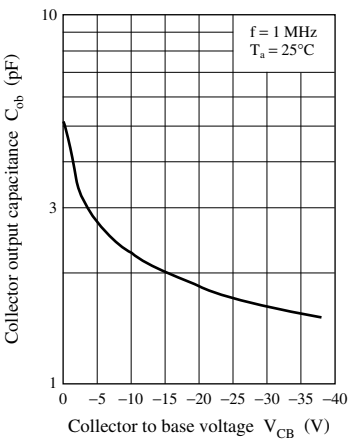
$V_{CE(sat)}$ — I_C



h_{FE} — I_C

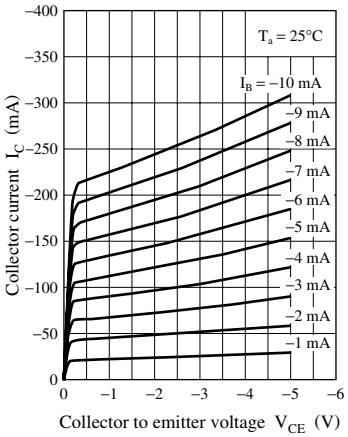


C_{ob} — V_{CB}

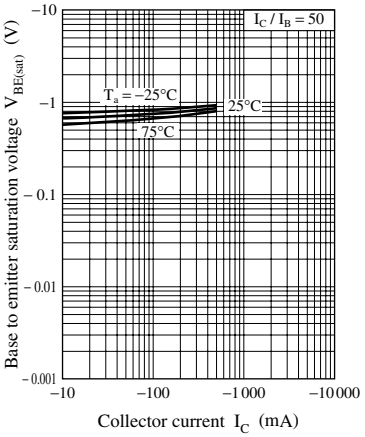


Characteristics chart of Tr2

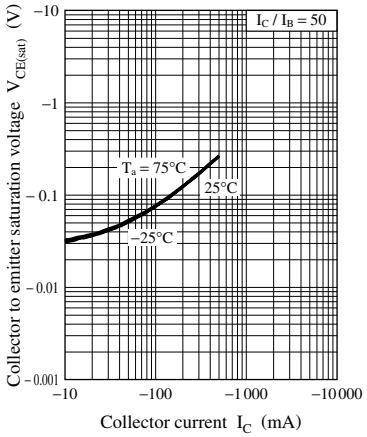
I_C — V_{CE}



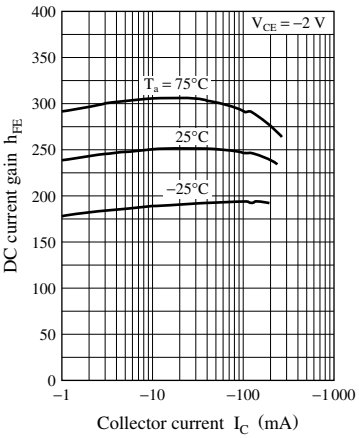
$V_{BE(sat)}$ — I_C



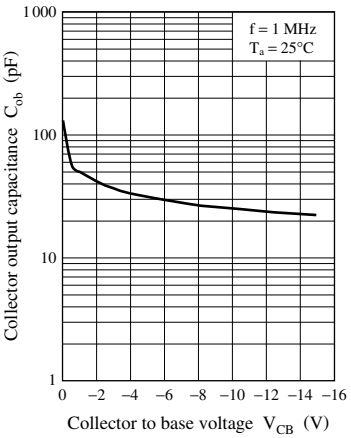
$V_{CE(sat)}$ — I_C



h_{FE} — I_C



C_{ob} — V_{CB}



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